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(71) Applicant:

SAMSUNG ELECTRONICS CO., LTD.

(72) Inventor:

KA, JAE HWAN

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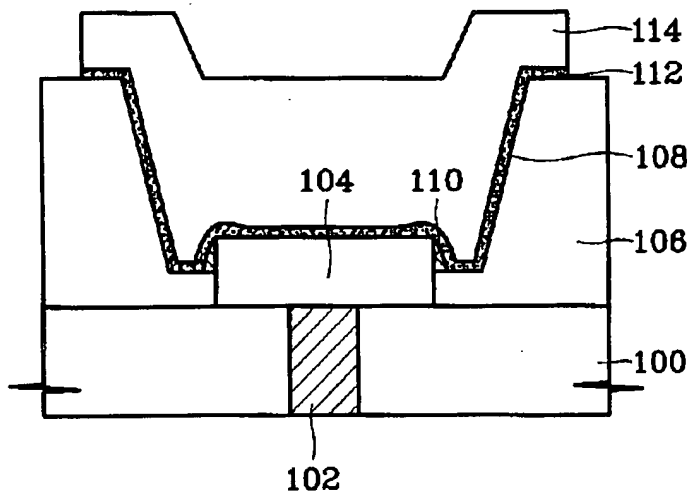
(54) Title of Invention

CAPACITOR OF METAL-INSULATOR-METAL STRUCTURE AND METHOD FOR FABRICATING THE SAME

Representative drawing

(57) Abstract:

PURPOSE: A capacitor of a metal-insulator-metal structure and a method for fabricating the same are provided to prevent leakage current by forming uniformly a dielectric layer and improving a step coverage.



CONSTITUTION: A lower electrode layer and a photoresist layer are sequentially coated on the first interlayer dielectric(100) on which a contact plug(102) is formed. A photoresist pattern is formed to define a lower electrode (104) on the photoresist layer. The lower electrode layer is etched by using the photoresist pattern as an etch mask and the lower electrode(104) is formed thereby. The second interlayer dielectric(106) is formed on the lower electrode(104). An aperture(108) is formed by etching the second interlayer dielectric(106). A dielectric layer(112) is formed on a whole surface of the above structure by using a chemical vapor deposition method. The dielectric layer(112) is formed by an oxide layer, a nitride layer, and a mixed layer of the oxide and the nitride. An upper electrode(114) is formed thereon. The upper electrode(114) is formed by a metal layer, a metal oxide layer or a mixed layer of the metal and the metal oxide.

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